TOSHIBA

2SA1802

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2SA1802

STROBE FLASH APPLICATIONS MEDIUM POWER AMPLIFIER APPLICATIONS

Excellent hFE Linearity

: $h_{FE (1)} = 200 \sim 600 \text{ (V}_{CE} = -2 \text{ V, I}_{C} = -0.5 \text{ A)}$: $h_{FE (2)} = 140 \text{ (Min.) (V}_{CE} = -2 \text{ V, I}_{C} = -3 \text{ A)}$

Low Collector Saturation Voltage

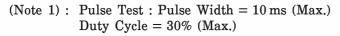
 $: V_{CE (sat)} = -0.5 \text{ V (Max.)} (I_{C} = -3 \text{ A}, I_{B} = -60 \text{ mA})$

Surface Mount Package: Lead Bending Type 2-7B2A

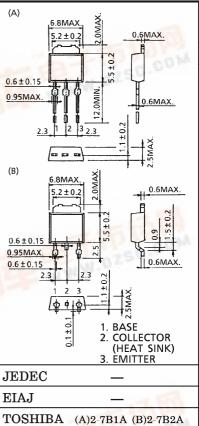
Complementary to 2SC4681

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACT	SYMBOL	RATING	UNIT		
Collector-Base Volt	v_{CBO}	-30	V		
Collector-Emitter V	VCES	-30	V		
Conector-Emitter V	V_{CEO}	-10			
Emitter-Base Volta	$V_{ m EBO}$	-6	V		
Collector Current	\mathbf{DC}	$I_{\mathbf{C}}$	-3	A	
	Pulsed (Note 1)	ICP	- 6		
Base Current	IB	-0.5	Α		
Collector Power Ta = 25°C		150.	1.0	w	
Dissipation	$Tc = 25^{\circ}C$	$^{\mathrm{P}_{\mathrm{C}}}$	10] **	
Junction Temperat	T_{j}	150	°C		
Storage Temperatu	$ m T_{stg}$	-55~150	°C		



Unit in mm



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

lf.dzsc.com

	(: = == =,					
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = -30 \text{ V}, I_{E} = 0$	_	_	-100	nA
Emitter Cut-off Current	IEBO	$V_{EB} = -6 \text{ V}, I_{C} = 0$	_	_	-100	nA
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\mathrm{C}}=-10\mathrm{mA},~I_{\mathrm{B}}=0$	-10	_		V
DC Current Gain	h _{FE (1)}	$V_{CE} = -2 V, I_{C} = -0.5 A$	200		600	MO
	h _{FE (2)}	$V_{CE} = -2 V, I_{C} = -3 A$	140	200	66.	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{\rm C} = -3 {\rm A}, I_{\rm B} = -60 {\rm mA}$	ΨV	-0.25	-0.50	v
Base-Emitter Voltage	$v_{ m BE}$	$V_{CE} = -2 V, I_{C} = -3 A$	_	-0.86	-1.2	V
Transition Frequency	f_{T}	$V_{CE} = -2 \text{ V}, I_{C} = -0.5 \text{ A}$	_	180	_	MHz
Collector Output Capacitance	Coh	$V_{CB} = -10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	50	_	рF

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

The information contained herein is subject to change without notice.